4. (Once Amended) A method of etching an organic dielectric layer over a substrate, comprising:

placing a hard mask over the organic dielectric layer;

placing a patterned photoresist layer over the hard mask layer;

placing the substrate in an etching chamber;

providing an etchant gas comprising NH3 into the etching chamber, wherein the NH3 has a flow rate between 5 sccm to 1500 sccm;

generating a plasma from the NH3, which etches the organic dielectric layer; and

simultaneously stripping the photo resist layer during the etching of the organic dielectric layer.

5. The method, as recited in claim 4, further comprising providing CH3F while providing the etchant gas comprising NH3.

6. The method, as recited in claim 5, wherein the CH3F has a flow rate between 1 sccm to 50 sccm.

7. The method, as recited in claim 6, further comprising providing an etch with an etchant gas comprising CF4, prior to the step of providing the etchant gas comprising NH3.

8. The method, as recited in claim 7, wherein the etchant gas comprising CF4, further comprises C4F8.

9. The method, as recited in claim 8, wherein the etchant gas comprising CF4 further comprises O2.

10. The method, as recited in claim 9, wherein the O2 has a flow rate of between 3 sccm and 300 sccm.

11. The method, as recited in claim 10, wherein the organic dielectric layer is made of an organic low-k material.

12. (Cancelled)

13. (Once Amended) A method of etching an organic dielectric layer over a substrate, comprising:

placing a hard mask over the organic dielectric layer;

placing a patterned photoresist layer over the hard mask layer;

placing the substrate in an etching chamber;

providing an etchant gas comprising NH3 into the etching chamber;

generating a plasma from the NH3, which etches the organic dielectric layer; and

simultaneously stripping the photo resist layer during the etching of the organic dielectric layer.

14. The method, as recited in claim 1, further comprising providing CH3F while providing the etchant gas comprising NH3.

15. The method, as recited in claim 14, further comprising providing an etch with an etchant gas comprising CF_4, prior to the step of providing the etchant gas comprising NH_3.

16. The method, as recited in claim 1, wherein the organic dielectric layer is made of an organic low-k material.

17. (Cancelled)

18. (Cancelled)

19. (Cancelled)

20. (New) The method, as recited in claim 13, wherein the NH_3 has a flow rate, wherein the flow rate of NH_3 is from about 100 sccm to about 1000 sccm.

21. (New) The method, as recited in claim 13, wherein the NH_3 has a flow rate from about 300 sccm to about 800 sccm.

22. (New) The method, as recited in claim 21, further comprising maintaining the substrate at a temperature between about 10^{o} C to about 40^{o} C during etching of the organic dielectric layer.

23. (New) The method, as recited in claim 22, further comprising providing a power input of between about 250 W to about 1000 W.

24. (New) A method of etching an organic dielectric layer disposed below a hardmask layer and over a substrate, comprising:

placing the substrate in an etching chamber;

providing an etchant gas comprising NH3 into the etching chamber with a flow rate from about 300 sccm to about 800 sccm;

generating a plasma from the NH3, which etches the organic dielectric layer; and

maintaining the substrate at a temperature between about 10^{0} C to about 40^{0} C during the etching of the organic dielectric layer.